Appl. No. 10/092,465

Amdt. Dated January 20, 2004

Reply to Office action of October 17, 2003

## **Listing of Claims:**

- 1. (Canceled)
- 2. (Canceled)
- 3. (Canceled)
- 4. (Canceled)
- 5. (Canceled)
- 6. (Canceled)
- 7. (Canceled)
- 8. (Canceled)
- 9. (Currently amended) A platinum sputtering target material, wherein said target material containing contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (200) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder platinum sample.
- 10. (Currently amended) A ruthenium sputtering target material, wherein said target material containing contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (112) face to that of another arbitrary crystal face as determined

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by X-ray diffractometry is greater than the corresponding ratio as measured for a powder ruthenium sample.

- 11. (Currently amended) A ruthenium sputtering target material, wherein said target material containing contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (002) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder ruthenium sample.
- 12. (Currently amended) A ruthenium sputtering target material, wherein said target material containing contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (004) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder ruthenium sample.
- 13. (Currently amended) An iridium sputtering target material, wherein said target material containing contains columnar crystals grown in a direction normal to a sputtering surface, and a ratio of an integral intensity of a (220) face to that of another arbitrary crystal face as determined by X-ray diffractometry is greater than the corresponding ratio as measured for a powder iridium sample.
- 14. (Previously presented) A sputtering target material according to claim 9, wherein a crystallographic microstructure containing the columnar crystals is electrodeposited from a solution containing a precious metal salt.
- 15. (Previously presented) A sputtering target material according to claim 10, wherein a crystallographic microstructure containing <u>the</u> columnar crystals is electrodeposited from a solution containing a precious metal salt.

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16. (Previously presented) A sputtering target material according to claim 11, wherein a crystallographic microstructure containing <u>the</u> columnar crystals is electrodeposited from a solution containing a precious metal salt.

- 17. (Previously presented) A sputtering target material according to claim 12, wherein a crystallographic microstructure containing the columnar crystals is electrodeposited from a solution containing a precious metal salt.
- 18. (Previously presented) A sputtering target material according to claim 13, wherein a crystallographic microstructure containing <u>the</u> columnar crystals is electrodeposited from a solution containing a precious metal salt.
- 19. (Canceled)
- 20. (Canceled)
- 21. (Canceled)
- 22. (Canceled)
- 23. (Canceled)